

Application

- Motor drive
- · Inverter, Converter
- · Photovoltaics, wind power generation.
- · Induction heating equipment.

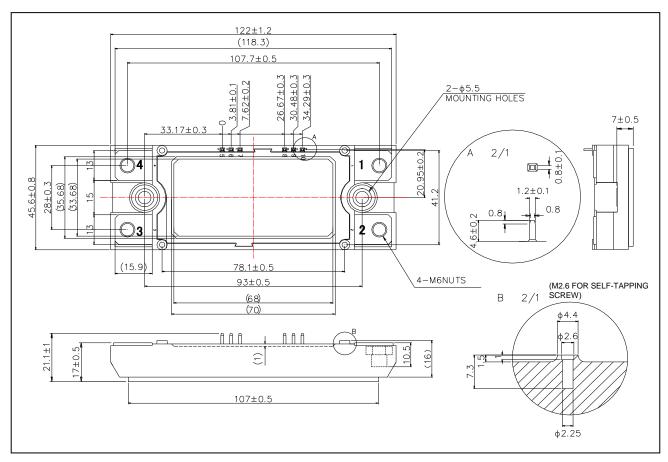
Features

- 1) Low surge, low switching loss.
- 2) High-speed switching possible.
- 3) Reduced temperature dependence.

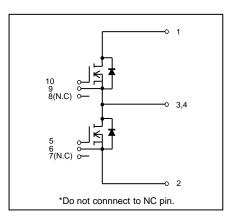
Construction

This product is a half bridge module consisting of SiC-DMOS from ROHM.

•Dimensions & Pin layout (Unit : mm)



Circuit diagram



Parameter	Symbol	Conditions	Limit	Unit
Drain-source voltage	V _{DSS}	G-S short	1200	V
Gate-source voltage(+)	V_{GSS}	D-S short	22	V
Gate-source voltage(-)		D-S short	-6	V
G - S Voltage (tsurge<300nsec	V _{GSSsurge}	D-S short	-10 to +26	°C
Drain current *1	I _D	DC(Tc=60°C)	204	Α
Drain current "	I _{DRM}	Pulse (Tc=60°C) 1ms *2	360	Α
Source current * ¹	I _S	Tc=60°C V _{GS} =18V	204	Α
	I _{SRM}	Pulse (Tc=60°C) 1ms V _{GS} =18V * ²	360	Α
		Pulse (Tc=60°C) 10µs V _{GS} =0V * ^{2*3}	1360	Α
Total power disspation *4	Ptot	Tc=25°C	175	W
Max Junction Temperature	Tjmax		-40 to150	°C
Storage temperature	Tstg		-40 to125	°C
Isolation voltage	Visol	sol Terminals to baseplate, f=60Hz AC 1min.		Vrms
Mounting torque		Main Terminals : M6 screw	4.5	N·m
	_	Mounting to heat shink : M5 screw	3.5	N·m

•Absolute maximum ratings (Tj = 25°C)

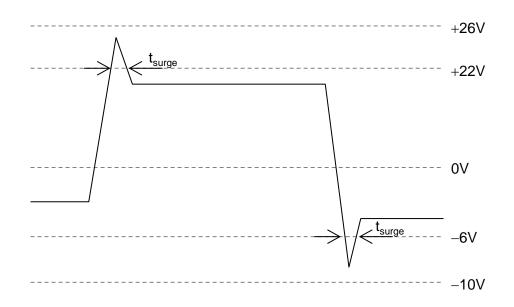
(*1) Measurement of Tc is to be done at the point just under the chip.

(*2) Repetition rate should be kept within the range where temperature rise of die should not exceed Tj max.

(*3) Duration of current conduction at gate-off state should not exceed 10μ sec.

(*4) Tj is less than 175°C

Example of acceptable VGS waveform



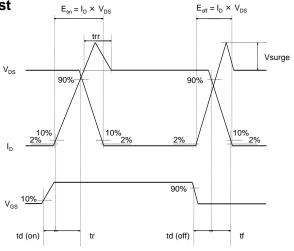
•Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Static drain-source on-state voltage	V _{DS(on)}	I _C =180A, V _{GS} =18V	Tj=25°C	-	2.3	3.2	V
			Tj=125°C	-	3.3	4.4	
			Tj=150°C	-	3.6	5	
Drain cutoff current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V		-	-	10	μA
Source-drain voltage	V _{SD}	V _{GS} =0V, I _S =180A	Tj=25°C	-	5.4	-	V
			Tj=125°C	-	5.1	-	
			Tj=150°C	-	4.8	-	
		V _{GS} =18V, I _S =180A	Tj=25°C	-	2.3	-	
			Tj=125°C	-	3.3	-	
			Tj=150°C	-	3.5	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =10V, I _D =35.2mA		1.6	2.7	4	V
Gate-source leakage current	I _{GSS}	V _{GS} =22V, V _{DS} =0V		-	-	0.5	μA
		$V_{GS} = -6V, V_{DS} = 0V$		-0.5	-	-	
Switching characteristics	td(on)	V _{GS(on)} =18V, V _{GS(off)} =0V		-	80	-	ns
	tr	V _{DS} =600V		-	90	-	
	trr	I _D =180A		-	50	-	
	td(off)	R _G =5.6Ω		-	300	-	
	tr	inductive load		-	90	-	
Input capacitance	Ciss	V _{DS} =10V, V _{GS} =0V, f=1MHz		-	23	-	nF
Internal gate resistor	R _{Gint}	Tj=25°C		-	1.15	-	Ω
Stray Inductance	Ls			-	25	-	nH
Oracana Distance	-	Terminal to heat sink		-	11.5	-	mm
Creepage Distance		Terminal to terminal		-	19.0	-	mm
Clearance Distance	-	Terminal to heat sink		-	9.5	-	mm
		Terminal to terminal		-	13.0	-	mm
Junction-to-case thermal resistance	Rth(j-c)	DMOS (1/2 module) * ⁵		-	-	0.11	°C/W
Case-to-heat sink Thermal resistance	Rth(c-f)	Case to heat sink, per 1 module, Thermal grease appied * ⁶		-	0.035	-	

(*5) Measurement of Tc is to be done at the point just beneath the chip.

(*6) Typical value is measured by using thermally conductive grease of λ =0.9W / (m · K).

•Waveform for switching test



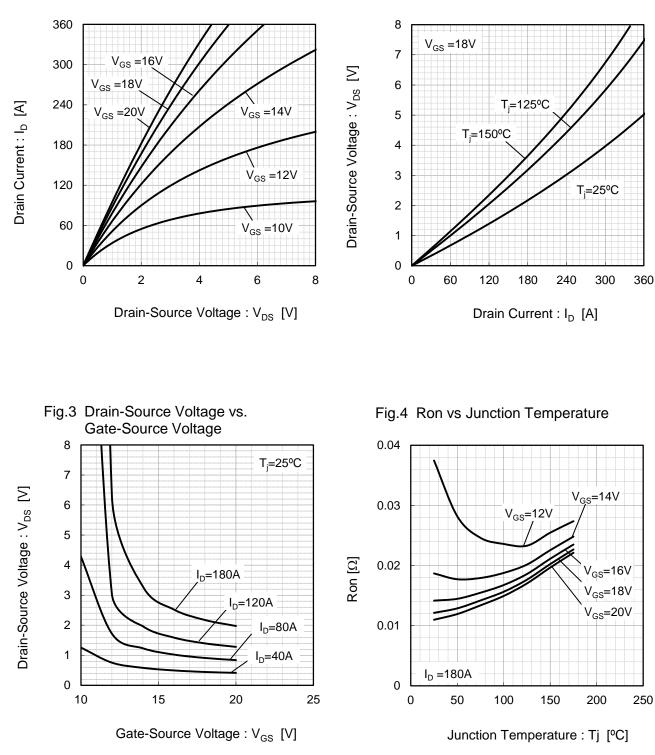


Fig.1 Typical Output Characteristics

Fig.2 Drain-Source Voltage vs. Drain Current

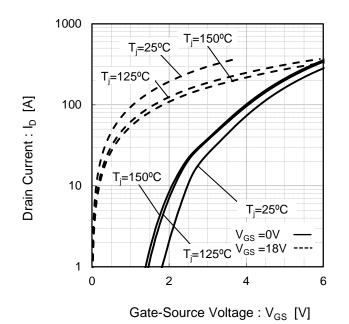
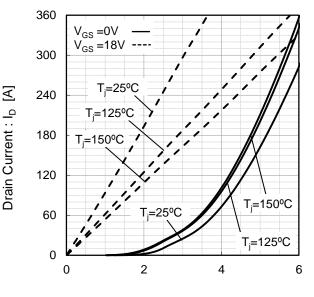


Fig.5 Drain Current vs. Gate-Source Voltage

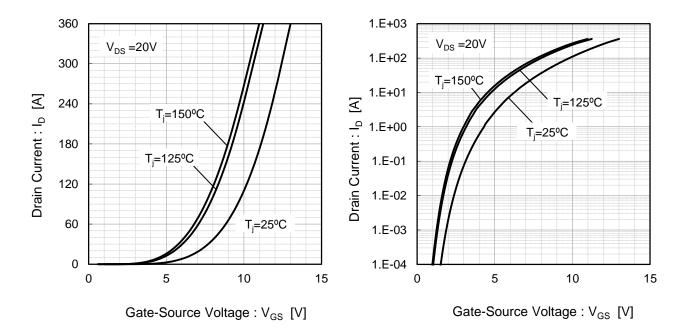
Fig.6 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.7 Drain Current vs. Gate-Source Voltage

Fig.8 Drain Current vs. Gate-Source Voltage



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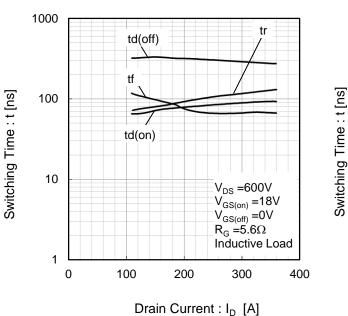
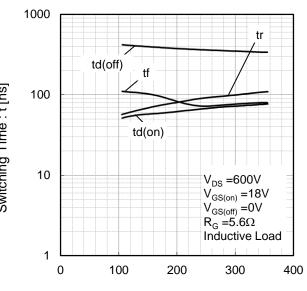
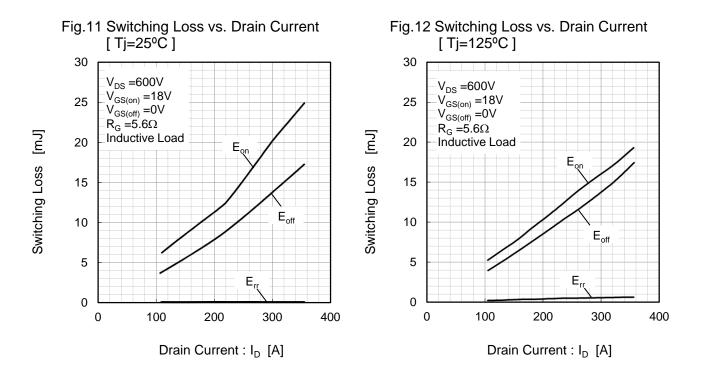


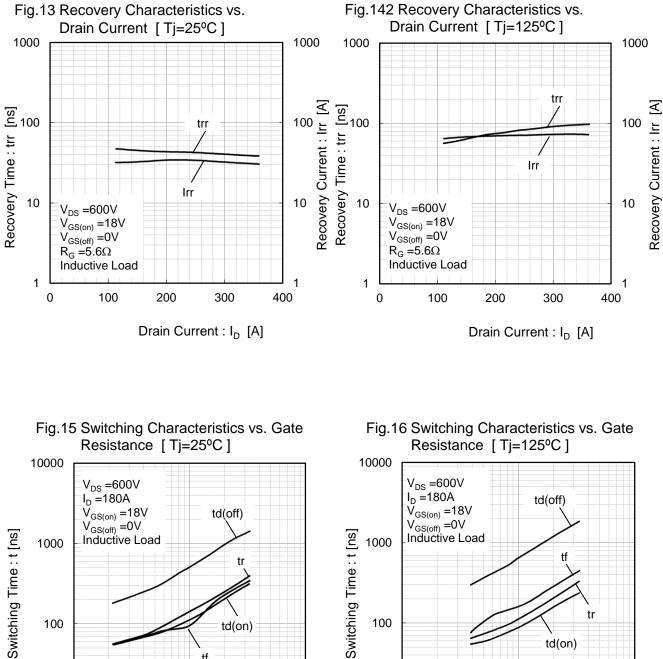
Fig.9 Switching Characteristics [Tj=25°C]

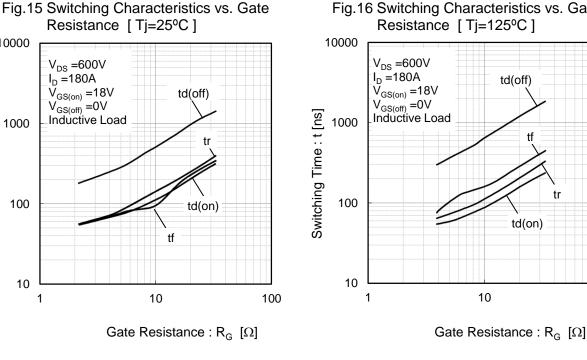
Fig.10 Switching Characteristics [Tj=125°C]



Drain Current : I_D [A]







tr

100

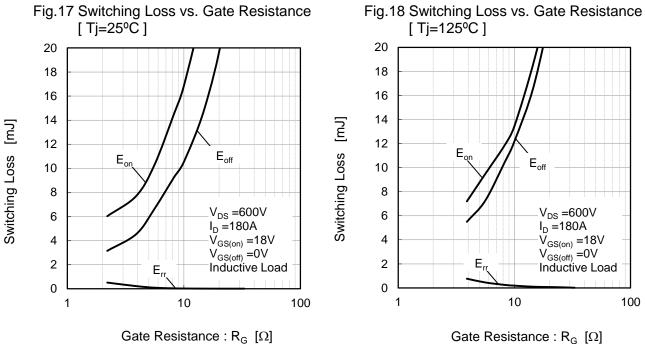
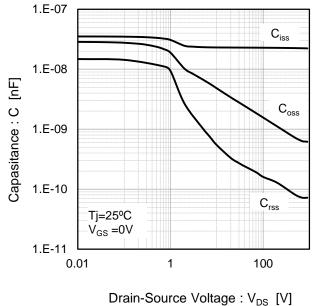
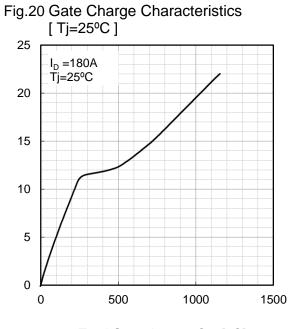


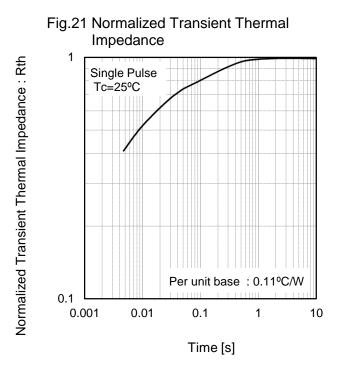
Fig.19 Typical Capacitance vs. Drain-Source Voltage





Total Gate charge : Qg [nC]

Gate-Source Voltage : V_{GS} [V]



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